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#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C		
-60V	125m $\Omega$ @ V <sub>GS</sub> = -10V	-3.4A		
	190mΩ @ V <sub>GS</sub> = -4.5V	-2.8A		

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

### **Features and Benefits**

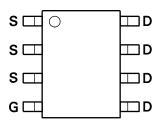
- · Fast switching speed
- Low input capacitance
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

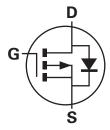
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)







Top View



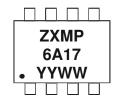
**Equivalent Circuit** 

### Ordering Information (Note 1)

Ī	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
	ZXMP6A17N8TC	See below	13	12	2,500	

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## **Marking Information**



ZXMP = Product Type Marking Code, Line 1 6A17 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01 - 53)





### Maximum Ratings @TA = 25°C unless otherwise specified

	Characteristic		Symbol	Value	Unit
Drain-Source voltage			$V_{DSS}$	-60	V
Gate-Source voltage			$V_{GS}$	±20	V
		(Note 3)		-3.42	
Continuous Drain current	$V_{GS} = 10V$	$T_A = 70^{\circ}C$ (Note 3)	I <sub>D</sub>	-2.73	Α
		(Note 2)		-2.7	
Pulsed Drain current $V_{GS} = 10V$		(Note 4)	$I_{DM}$	-15.6	Α
Continuous Source current (Body diode) (Note 3		(Note 3)	Is	-3.4	Α
Pulsed Source current (Body diode) (Note 4)		(Note 4)	I <sub>SM</sub>	-15.6	А

### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Power dissipation	(Note 2)		1.56 12.5	W	
Linear derating factor	(Note 3)	P <sub>D</sub>	2.5 20	mW/°C	
Thermal Desistance Junction to Ambient	(Note 2)	Б	80		
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	50	°C/W	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{ heta JL}$	32		
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	

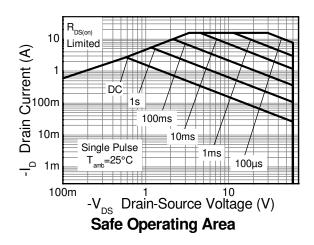
Notes:

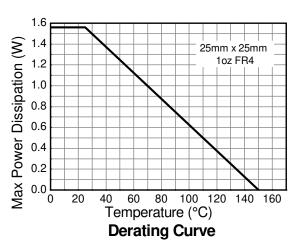
- 2. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 3. Same as note (2), except the device is measured at  $t \le 10$  sec.
- 4. Same as note (2), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.

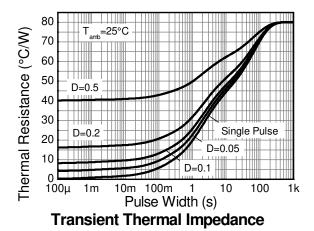
  5. Thermal resistance from junction to solder-point (at the end of the drain lead).

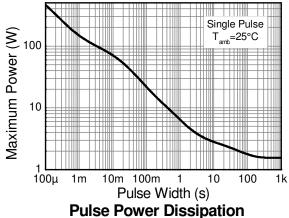


### **Thermal Characteristics**













## Electrical Characteristics @TA = 25°C unless otherwise specified

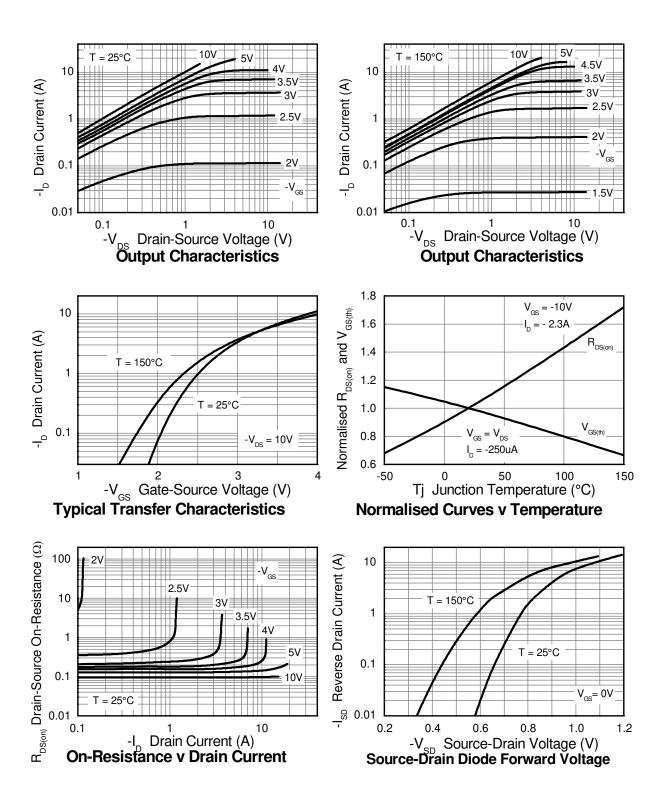
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60			V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0			V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 6)				0.125	Ω	$V_{GS} = -10V, I_D = -2.3A$	
Static Drain-Source On-Resistance (Note 0)	R <sub>DS (ON)</sub>	_		0.190	22	$V_{GS} = -4.5V, I_D = -1.9A$	
Forward Transconductance (Notes 6 & 7)	g <sub>fs</sub>	_	4.7		S	$V_{DS} = -15V, I_{D} = -2.3A$	
Diode Forward Voltage (Note 6)	$V_{SD}$	_	-0.85	-0.95	V	$I_S = -2.0A, V_{GS} = 0V$	
Reverse recovery time (Note 7)	t <sub>rr</sub>		25.1	_	ns	1 7 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
Reverse recovery charge (Note 7)	Qrr	_	27.2	_	nC	I <sub>S</sub> = -1.7A, di/dt = 100A/μs	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	_	637	_	pF	\	
Output Capacitance	Coss	_	70	_	рF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V -f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	53	_	pF	1 = 1101112	
Total Gate Charge (Note 8)	$Q_g$	_	9.0	_	nC	V <sub>GS</sub> = -4.5V	
Total Gate Charge (Note 8)	Qg	_	17.7	_	nC	V <sub>DS</sub> = -30V	
Gate-Source Charge (Note 8)	Q <sub>gs</sub>	_	1.6	_	nC	$V_{GS} = -10V$ $I_{D} = -2.2A$	
Gate-Drain Charge (Note 8)	$Q_{gd}$	_	4.4	_	nC	]	
Turn-On Delay Time (Note 8)	t <sub>D(on)</sub>	_	2.6	_	ns	·	
Turn-On Rise Time (Note 8)	t <sub>r</sub>	_	3.4	_	ns	$V_{DD} = -30V, V_{GS} = -10V$	
Turn-Off Delay Time (Note 8)	t <sub>D(off)</sub>	_	26.2	_	ns	$I_D = -1A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 8)	t <sub>f</sub>	_	11.3	_	ns		

Notes:

- Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
   For design aid only, not subject to production testing.
   Switching characteristics are independent of operating junction temperatures.

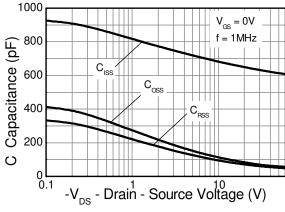


## **Typical Characteristics**

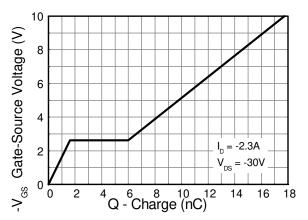




# **Typical Characteristics - continued**

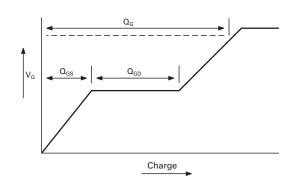


Capacitance v Drain-Source Voltage

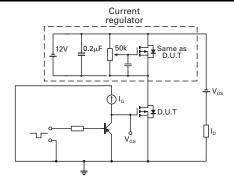


Gate-Source Voltage v Gate Charge

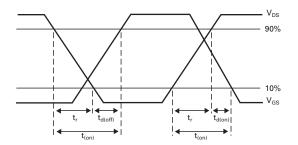
# **Test Circuits**



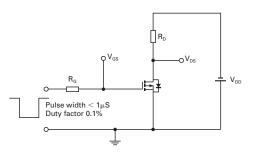
Basic gate charge waveform



Gate charge test circuit



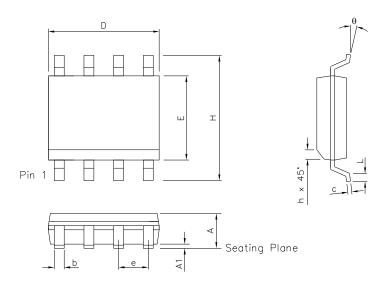
Switching time waveforms



Switching time test circuit

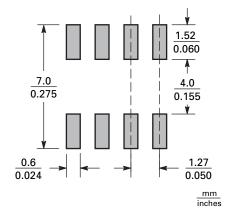


# **Package Outline Dimensions**

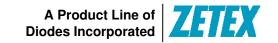


DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.053	0.069	1.35	1.75	е	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	С	0.008	0.010	0.19	0.25
Н	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
Е	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

# **Suggested Pad Layout**







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